



Latin American Electron Devices Conference
Armenia, Quindio, Colombia. February 24-27, 2019



Latin American Electron Devices Conference

February 24-29, 2019

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Technical Program



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Table of contents

Message from the conference chairs

Conference Program

Workshops

MOS-AK Workshop on Compact Modeling	1
-------------------------------------	---

EDS Minicolloquium	2
--------------------	---

Keynote Speakers

- | | | |
|----|--|----|
| K1 | Adrian Ionescu "Will Democratic Artificial Intelligence Shape the Future of Semiconductor Technology?" | 9 |
| K2 | Hiroshi Iwai "End of CMOS miniaturization and technology development after that" | 10 |

Device Physics

- | | | |
|----|---|----|
| A1 | RF and DC degradation of a SOI FET technology.
Edmundo A. Gutierrez-D., Jairo Mendez, Julio Tinoco and Emmanuel Torres-R. | 11 |
| A2 | Analysis of Vias Position on the BEOL Temperature Distribution.
Rafael Nunes, Jose Bohorquez and Roberto Orio. | 15 |
| A3 | IoT Circuit Design to Monitor Cold Chain Refrigerators
Oscar De Jesús Ballestas Ortega, José Luis Villa Ramírez and Edgar David Villa Pérez | 19 |
| A4 | Study of the properties of transport in semiconductor devices due to the effect of the static magnetic field.
Adrian I. Tec Chim, Oscar Huerta and Edmundo Gutierrez | 24 |

A5	Antennas Design for UHF Passive RFID Tags. Jorge Daniel Terán Guerra, Jaime Martínez Castillo and Raul López Leal	27
A6	The magnetic field impact on the 1/f noise and the charge-pumping measurements in MOSFETs. Oscar Vicente Huerta Gonzalez, Adrian I. Tec-Chim and Edmundo Gutierrez.	31
A7	Memristors: A perspective and impact on the electronics industry. Alexander Vera, Jorge Marin and Marisol Gomez	35

Devices and Materials

D1	Effect of Drain Top Metal Overlap on the Current in Bottom-gate Thin Film Transistors. Magali Estrada, Isai Hernandez, Yoanlys Hernandez-Barrios, Matteo Rapisarda, Antonio Valletta, Luigi Marucci and Antonio Cerdeira	39
D2	Comparison of Different Technologies for Transistor Rectifiers Circuits for Micropower Energy Harvesters. Luis-Miguel Procel-Moya, John Paredes and Lionel Trojman	43
D3	Substrate influence on Bi ₂ Te ₃ growth by MBE. Omar Concepción Díaz, Osvaldo de Melo and Arturo Escobosa	47
D4	High Efficient Inverted Polymer Solar Cells with Solution-Processed Electron Transport Layer. José G. Sánchez, Víctor S. Balderrama, Magali Estrada, Josep Pallarès and Lluis F. Marsal	50
D5	Origin of the Negative Differential Resistance in the output characteristics of a picene-based Thin-Film Transistor. Joaquin Puigdollers, Eloi Ros, Pablo Ortega and Cristobal Voz	53
D6	Degradation Study of Inverted Polymer Solar Cells Using Inkjet Printed ZnO Electron Transport Layer. Angel Sacramento, Magaly Ramírez, Victor Balderrama, Ivan Garduño, Magali Estrada and Lluis Marsal	57
D7	Graphene oxide multilayers: Synthesis, properties and possible applications in electronic. Jhon Jairo Prías Barragán, Katherine Gross, Hernando Ariza Calderónand Pedro Prieto Pulido.	61
D8	Microfluidic sub-Terahertz sensor for on-line determination of ethanol concentration in binary liquid mixtures. Salomão Moraes da Silva, Johan Stein and Jacobus Swart	65

Modeling

M1	UMEM based 1/f noise model for amorphous ESL IGZO TFTs. Wondwosen Eshetu Muhea, Thomas Gneiting and Benjamin Iñiguez	68
M2	Full SPICE Simulation of a CMOS Active Pixel Sensor with Generalized Devices. Chiara Rossi and Jean-Michel Salles	72

M3	Parameter extraction and modeling of OTFTS from 150K to 300K. Harold Cortes-Ordonez, Clara Haddad, Stephanie Jacob, Gerad Ghibaudo, Firas Mohamed, Magali Estrada, Antonio Cerdeira and Benjamin Iniguez	76
M4	Charge-Based Compact Modeling of Capacitances in Staggered OTFTs. Jakob Leise, Jakob Pruefer, Ghader Darbandy and Alexander Kloes	80
M5	Resistive Switching Model of OxRAM Devices Based on Intrinsic Electrical Parameters. Silvana Guitarra, Lionel Trojman and Laurent Raymond	84
M6	Modeling Short-Channel Effects for Design by Hand with MOSFET Series Association. Eliyas Mehdiipour, Ademir Costa, Fabian de Andrade, Maicon Pereira, Edson Santana and Ana Isabela Cunha	88
M7	Influence of fin width and back bias on the low- frequency noise of long channel SOI nanowires. Allan Molto, Bruna Paz and Marcelo Pavanello	92
M8	Verilog-A Implementation of Static and Dynamic Trigate Junctionless Nanowire Transistor Compact Model. Cláudio V Moreira, Renan Trevisoli and Marcelo Antonio Pavanello	96
M9	Modeling Dielectric Constant Variability in Aggregate Polymers from CV Measurements. Rosane Moura Dos Santos, Catherine Dehollain, Marco Mattavelli, Diego Barretino and Jean-Michel Salles	100
	Author index	104